

2SC4252 SILICON NPN EPITAXIAL PLANAR TYPE TRANSISTOR

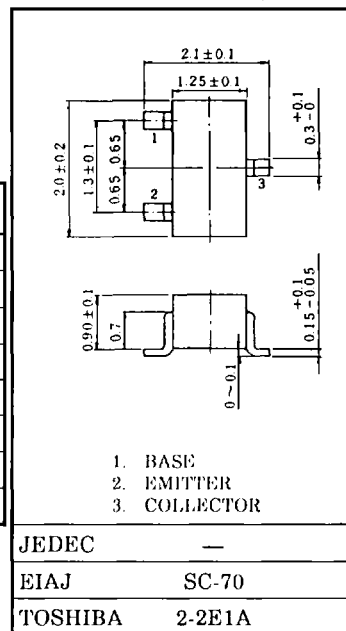
TV TUNER, VHF OSCILLATOR APPLICATIONS. (COMMON COLLECTOR)

Unit in mm

- Transition Frequency is High and Dependent on Current Excellently.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	20	V
Collector-Emitter Voltage	V _{CEO}	12	V
Emitter-Base Voltage	V _{EBO}	3	V
Base Current	I _B	15	mA
Collector Current	I _C	30	mA
Collector Power Dissipation	P _C	100	mW
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	-55~125	°C



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Weight : 0.006g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CBO}	V _{CB} = 20V, I _E = 0	—	—	0.1	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 3V, I _C = 0	—	—	1.0	μA
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C = 1mA, I _B = 0	12	—	—	V
DC Current Gain	h _{FE}	V _{CE} = 10V, I _C = 5mA	40	100	250	—
Transition Frequency	f _T	V _{CE} = 10V, I _C = 5mA, f = 500MHz	1.5	2.1	—	GHz
Output Capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f = 1MHz	—	1.1	1.4	pF
Collector-Base Time Constant	C _{c-rbb'}	V _{CB} = 10V, I _C = 5mA, f = 30MHz	—	4.3	10	ps

Marking

